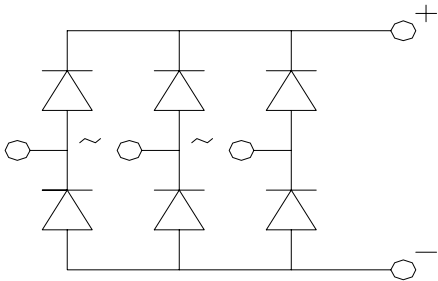


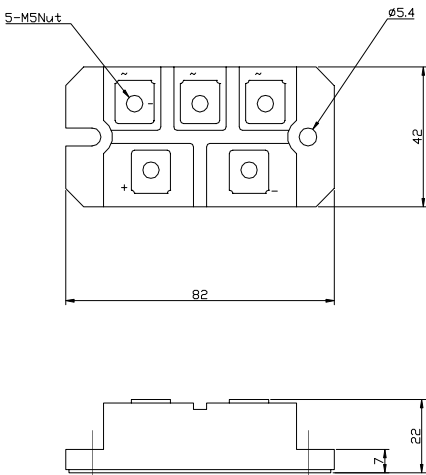
PT100S8

DIODE
 100A(Avg) 800Volts

■回路図 Circuit



■外形図 OUTLINE



■最大定格/ Maximum Ratings

■質量： Approx Net Weight:180g

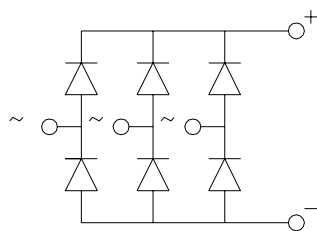
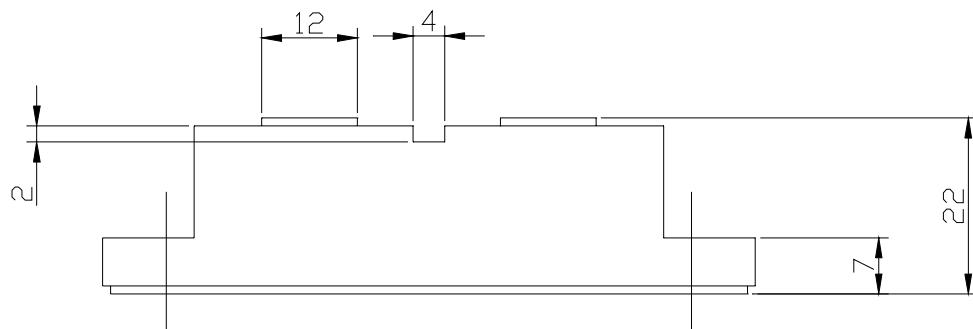
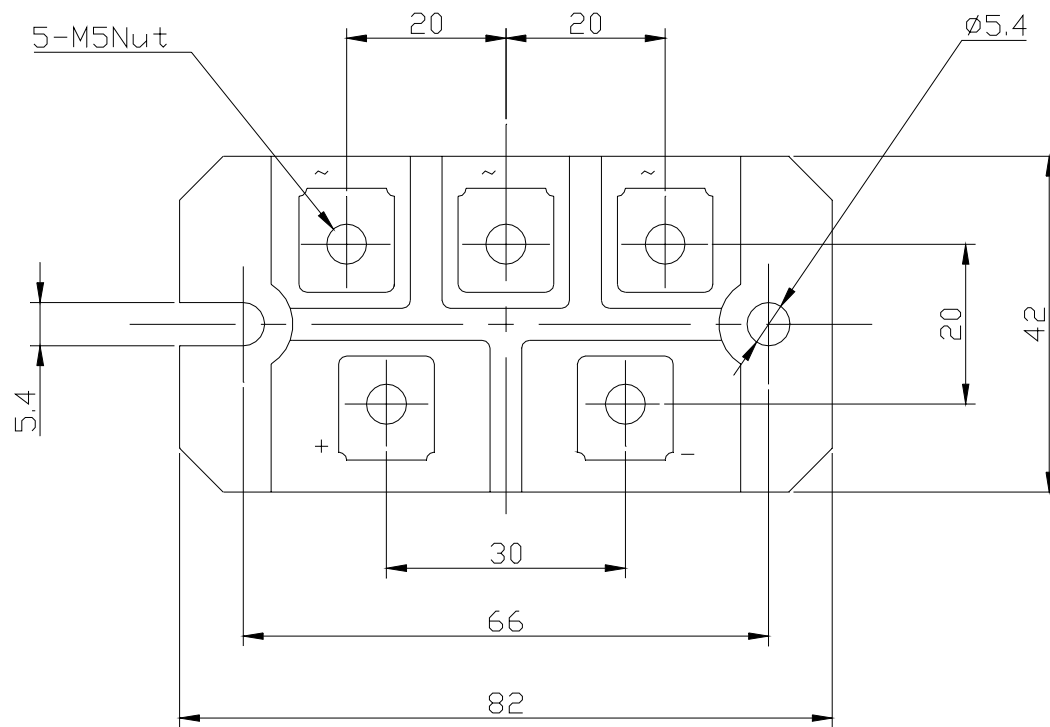
Rating		Symbol	PT100S8		Unit	
くり返しピーク逆電圧 *1 Repetitive Peak Reverse Voltage		V _{RRM}	800		V	
非くり返しピーク逆電圧 *1 Non Repetitive Peak Reverse Voltage		V _{RSM}	1000			
平均整流電流 Average Rectified Output Current		I _{O(AV)}	三相全波整流Tc=Tt(Terminal)=94℃ 3-Phase Full Wave Rectified	100	A	
サージ順電流 *1 Surge Forward Current		I _{FSM}	50 Hz Half Sine Wave,1Pulse Non-repetitive	1000	A	
電流二乗時間積 I Squared t		I ² t	2msec to 10msec	5000	A ² s	
動作接合温度範囲 Operating JunctionTemperature Range		T _{jw}	-40 to +150		℃	
保存温度範囲 Storage Temperature Range		T _{stg}	-40 to +125		℃	
絶縁耐圧 Isoration Voltage		Viso	端子 - 裏面ベース間,AC 1 分間 Base Plate to Terminals, AC1min	2500	V	
締付トルク Mounting torque	ベース部(mounting)	F _{tor}	推奨値 Recommended value	M5	2.4 to 2.8	N・m
	主端子部(Terminals)			M5	2.4 to 2.8	

■電氣的・熱的特性/ Electrical • Thermal Characteristics

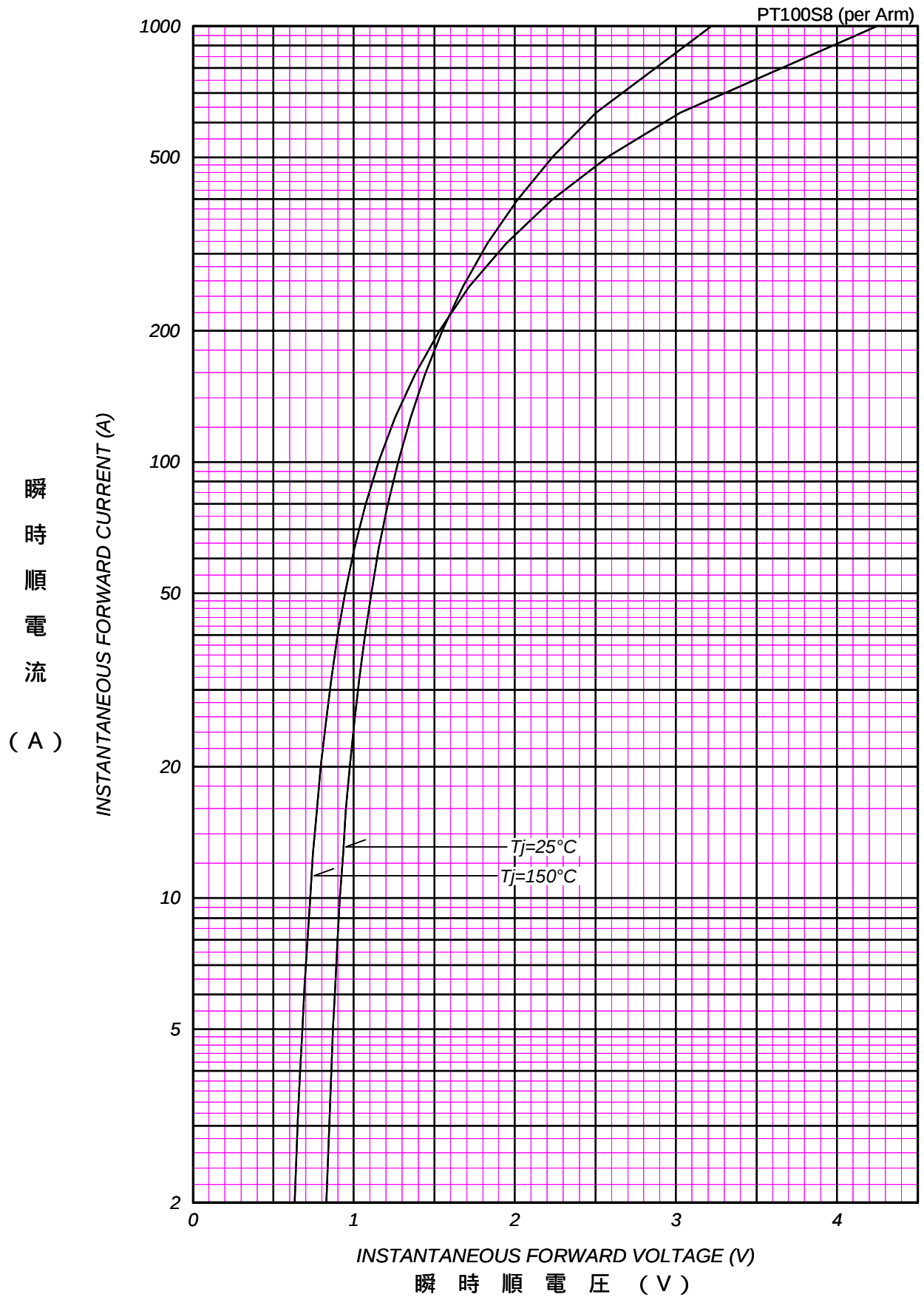
Characteristics	Symbol	Conditions	Max.	Unit
ピーク逆電流 *1 Peak Reverse Current	I _{RM}	V _{RM} = V _{RRM} , T _j = 150℃	10	mA
ピーク逆電圧 *1 Peak Forward Voltage	V _{FM}	I _{FM} = 100A, T _j =25℃	1.28	V
熱抵抗 Thermal Resistance	R _{th(j-c)}	接触部・ケース間 (トータル) Junction to Case (Total)	0.24	℃/W
接触熱抵抗 Thermal Resistance	R _{th(c-f)}	ケース・フィン間、サーマルコンパウンド塗布 Base Plate to Heat Sink with Thermal Compound (Total)	0.06	

*1: 1 アーム当たりの値 Value Per 1Arm

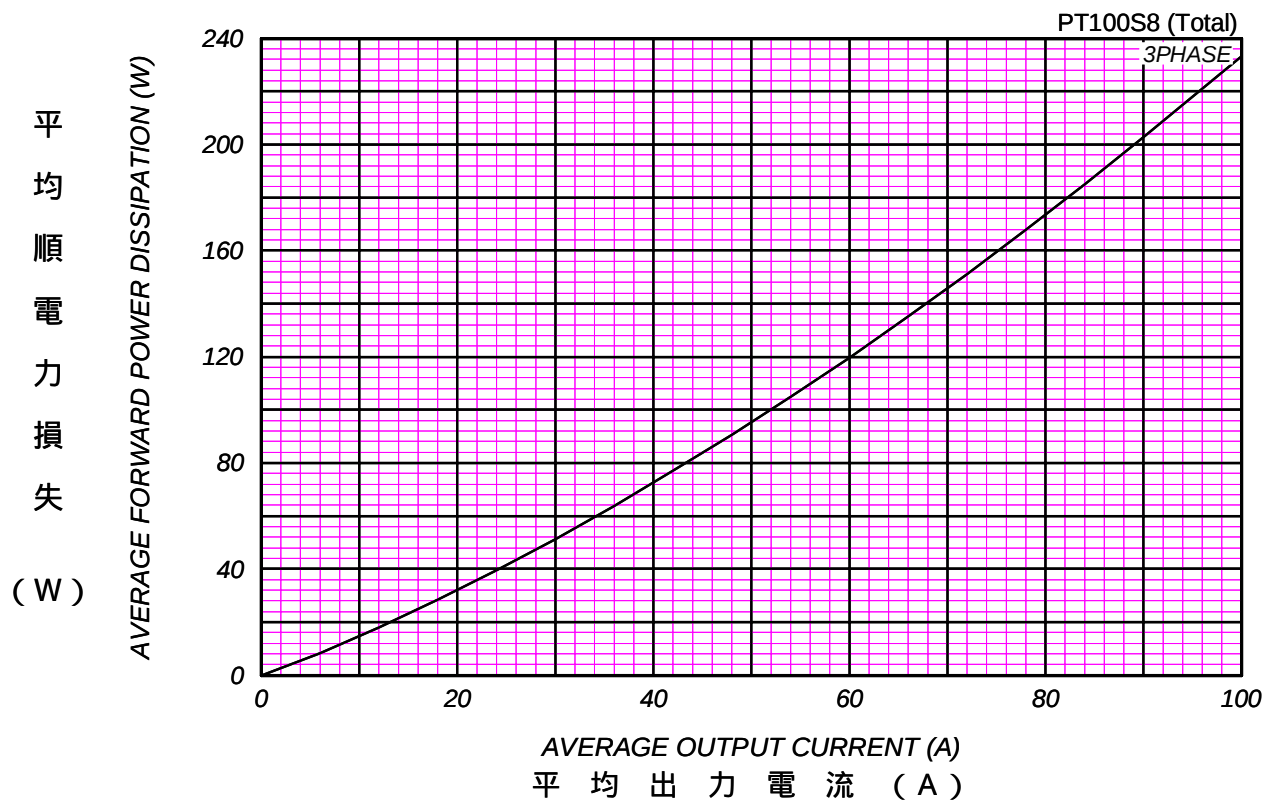
PT100S8 OUTLINE DRAWING (Dimensions in mm)



順電圧特性
FORWARD CURRENT VS. VOLTAGE

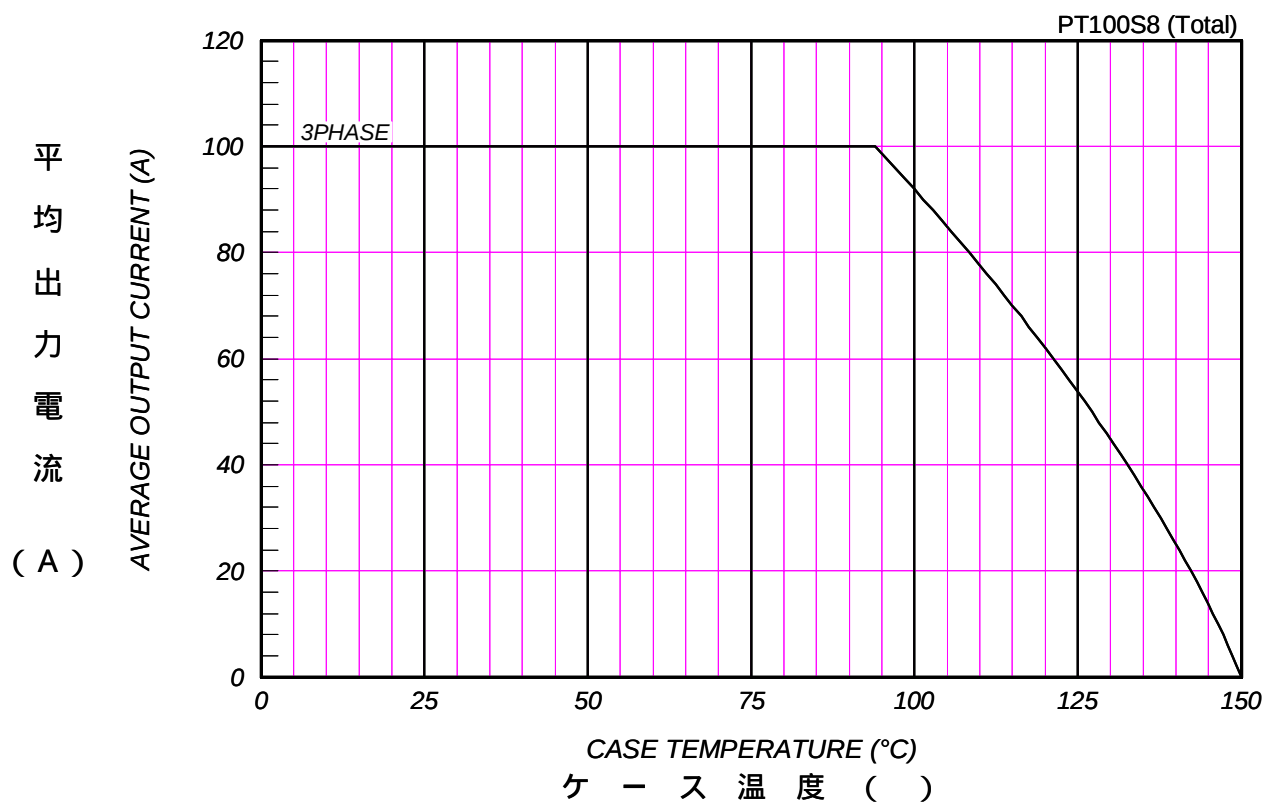


平均順電力損失特性
AVERAGE FORWARD POWER DISSIPATION



平均出力電流 - ケース温度定格
AVERAGE OUTPUT CURRENT VS. CASE TEMPERATURE

3-Phase Full Wave, Resistive or Inductive Load



サージ順電流定格
SURGE CURRENT RATINGS

f=50Hz, Harf Sine Wave, Non-Repetitive, Tj=150°C

PT100S8

サ
ー
ジ
順
電
流

(A)

SURGE FORWARD CURRENT (A)

